

Silicon Schottky Barrier Diode

HSM107S

■ Features

- Low V_F and high efficiency.
- HSM107S which is interconnected in series configuration is designed for protection from not only external excessive voltage but also miss-operation on electric systems.
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	8	V
Peak forward current	I_{FM}	0.1	A
Non-Repetitive Peak forward surge current	I_{FSM} (Note 1)	0.5	A
Average rectified current	I_o	50	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note

1. Square wave, 10ms

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V_R	$V_R = 1.0\text{ mA}$	8			pF
Reverse current	I_R	$V_R = 5\text{ V}$			30	μA
Forward voltage	V_F	$I_F = 10\text{ mA}$			0.3	V
ESD-Capability (Note 1)		$C=200\text{pF}$, Both forward and reverse direction 1 pulse.	100			V

Note

1. Failure criterion ; $I_R \geq 60\text{ }\mu\text{A}$ at $V_R = 5\text{ V}$

■ Marking

Marking	C5
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